

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-6. (Canceled)

7. (Currently Amended) A method for forming an underlayer ~~underlay~~-coating for use in manufacture of ~~semiconductora~~ semiconductor device, comprising:

coating an underlayer coating forming composition on a semiconductor substrate, wherein the underlayer coating forming composition comprises metal nitride particles having an average particle diameter of 1 to 1000 nm, and an organic solvent; and

baking the coated semiconductor substrate under a condition of a baking temperature of 80 to 300°C and a baking time of 0.5 to 10 minutes.

8. (Currently Amended) An underlayer coating for use in manufacture of ~~semiconductora~~ semiconductor device, formed by

coating an underlayer coating forming composition on a semiconductor substrate, wherein the underlayer coating forming composition comprises metal nitride particles having an average particle diameter of 1 to 1000 nm, and an organic ~~solvent~~,solvent; and

baking the coated semiconductor substrate under a condition of a baking temperature of 80 to 300°C and a baking time of 0.5 to 10 minutes.

9-10. (Canceled)